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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	25
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 9x12b; D/A 3x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f334k6t6

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Peripheral		STM32F334Kx	STM32F334Cx	STM32F334Rx				
	SPI	1						
Comm.	I ² C		1					
interfaces	USART	2		3				
	CAN		1					
GPIOs	Normal I/Os (TC, TTa)	10	20	26				
	5-Volt tolerant I/Os (FT,FTf)	15	17	25				
Capacitive s	ensing channels	14 17 18						
DMA channe	els	7						
12-bit ADCs		2	2	2				
Number of c	hannels	10	15	21				
12-bit DAC of	channels	3						
Ultra-fast an	alog comparator	2	2 3					
Operational	amplifiers	1						
CPU freque	ncy	72 MHz						
Operating vo	oltage	2.0 to 3.6 V						
Operating te	emperature	Ambient operatii Jun	mbient operating temperature: - 40 to 85 °C / - 40 to 105 °C Junction temperature: - 40 to 125 °C					
Packages		LQFP32	LQFP48	LQFP64				

Table 2. STM32F334x4/6/8 family device features and peripheral counts (continued)

1. This total considers also the PWMs generated on the complementary output channels.



3 Functional overview

3.1 ARM[®] Cortex[®]-M4 core with FPU with embedded Flash and SRAM

The ARM Cortex-M4 processor with FPU is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The ARM 32-bit Cortex-M4 RISC processor with FPU features exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allows efficient signal processing and complex algorithm execution.

Its single precision FPU speeds up software development by using metalanguage development tools, while avoiding saturation.

With its embedded ARM core, the STM32F334x4/6/8 family is compatible with all ARM tools and software.

Figure 1 shows the general block diagram of the STM32F334x4/6/8 family devices.

3.2 Memories

3.2.1 Embedded Flash memory

All STM32F334x4/6/8 devices feature up to 64 Kbytes of embedded Flash memory available for storing programs and data. The Flash memory access time is adjusted to the CPU clock frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above).

3.2.2 Embedded SRAM

The STM32F334x4/6/8 devices feature up to 12 Kbytes of embedded SRAM with hardware parity check. The memory can be accessed in read/write at CPU clock speed with 0 wait states, allowing the CPU to achieve 90 Dhrystone Mips at 72 MHz when running code from CCM (core coupled memory) RAM.

The SRAM is organized as follows:

- 4 Kbytes of SRAM on instruction and data bus with parity check (core coupled memory or CCM) and used to execute critical routines or to access data
- 12 Kbytes of SRAM with parity check mapped on the data bus.



remains in reset mode when the monitored supply voltage is below a specified threshold, VPOR/PDR, without the need for an external reset circuit.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated Option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the VPVD threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR), and power-down.

- The MR mode is used in the nominal regulation mode (Run)
- The LPR mode is used in Stop mode.
- The power-down mode is used in Standby mode: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The voltage regulator is always enabled after reset. It is disabled in Standby mode.

3.4.4 Low-power modes

The STM32F334x4/6/8 supports three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

• Stop mode

Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm, COMPx, I2C or USARTx.

Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.



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3.14.1 217 ps high-resolution timer (HRTIM1)

The high-resolution timer (HRTIM1) allows generating digital signals with high-accuracy timings, such as PWM or phase-shifted pulses.

It consists of 6 timers, 1 master and 5 slaves, totaling 10 high-resolution outputs, which can be coupled by pairs for deadtime insertion. It also features 5 fault inputs for protection purposes and 10 inputs to handle external events such as current limitation, zero voltage or zero current switching.

HRTIM1 timer is made of a digital kernel clocked at 144 MHz followed by delay lines. Delay lines with closed loop control guarantee a 217 ps resolution whatever the voltage, temperature or chip-to-chip manufacturing process deviation. The high-resolution is available on the 10 outputs in all operating modes: variable duty cycle, variable frequency, and constant ON time.

The slave timers can be combined to control multiswitch complex converters or operate independently to manage multiple independent converters.

The waveforms are defined by a combination of user-defined timings and external events such as analog or digital feedbacks signals.

HRTIM1 timer includes options for blanking and filtering out spurious events or faults. It also offers specific modes and features to offload the CPU: DMA requests, burst mode controller, push-pull and resonant mode.

It supports many topologies including LLC, Full bridge phase shifted, buck or boost converters, either in voltage or current mode, as well as lighting application (fluorescent or LED). It can also be used as a general purpose timer, for instance to achieve high-resolution PWM-emulated DAC.

In debug mode, the HRTIM1 counters can be frozen and the PWM outputs enter safe state.

3.14.2 Advanced timer (TIM1)

The advanced-control timer can be seen as a three-phase PWM multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead-times. They can also be seen as complete general-purpose timers. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIM timers (described in *Section 3.14.3* using the same architecture, so the advanced-control timers can work together with the TIM timers via the Timer Link feature for synchronization or event chaining.



SPI features ⁽¹⁾	SPI1
NSS pulse mode	Х
TI mode	х

Table 9. STM32F334x4/6/8 SPI implementation (continued)

1. X = supported.

3.16.4 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.17 Infrared transmitter

The STM32F334x4/6/8 devices provide an infrared transmitter solution. The solution is based on internal connections between TIM16 and TIM17 as shown in the figure below.

TIM17 is used to provide the carrier frequency and TIM16 provides the main signal to be sent. The infrared output signal is available on PB9 or PA13.

To generate the infrared remote control signals, TIM16 channel 1 and TIM17 channel 1 must be properly configured to generate correct waveforms. All standard IR pulse modulation modes can be obtained by programming the two timers output compare channels.





3.18 Touch sensing controller (TSC)

The STM32F334x4/6/8 devices provide a simple solution for adding capacitive sensing functionality to any application. These devices offer up to 18 capacitive sensing channels distributed over 6 analog I/Os group.

Capacitive sensing technology is able to detect the presence of a finger near an electrode which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle. It consists of

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Pi	n Numb	er			-	Pin	functions
LQFP 32	LQFP 48	LQFP 64	Pin name (function after reset)	Pin type	I/O structure	Alternate functions	Additional functions
-	27	35	PB14	I/O	ТТа	TIM15_CH1, TSC_G6_IO4, TIM1_CH2N, USART3_RTS_DE, HRTIM1_CHD1, EVENTOUT	ADC2_IN14, OPAMP2_VINP
-	28	36	PB15	I/O	ТТа	TIM15_CH2, TIM15_CH1N, TIM1_CH3N, HRTIM1_CHD2, EVENTOUT	ADC2_IN15, COMP6_INM, RTC_REFIN
-	-	37	PC6	I/O	FT	EVENTOUT, TIM3_CH1, HRTIM1_EEV10, COMP6_OUT	-
-	-	38	PC7	I/O	FT	EVENTOUT, TIM3_CH2, HRTIM1_FLT5	-
-	-	39	PC8	I/O	FT	EVENTOUT, TIM3_CH3, HRTIM1_CHE1	-
-	-	40	PC9	I/O	FT	EVENTOUT, TIM3_CH4, HRTIM1_CHE2	-
18	29	41	PA8	I/O	FT	MCO, TIM1_CH1, USART1_CK, HRTIM1_CHA1, EVENTOUT	-
19	30	42	PA9	I/O	FT	TSC_G4_IO1, TIM1_CH2, USART1_TX, TIM15_BKIN, TIM2_CH3, HRTIM1_CHA2, EVENTOUT	-
20	31	43	PA10	I/O	FT	TIM17_BKIN, TSC_G4_IO2, TIM1_CH3, USART1_RX, COMP6_OUT, TIM2_CH4, HRTIM1_CHB1, EVENTOUT	-
21	32	44	PA11	I/O	FT	TIM1_CH1N, USART1_CTS, CAN_RX, TIM1_CH4, TIM1_BKIN2, HRTIM1_CHB2, EVENTOUT	-
22	33	45	PA12	I/O	FT	TIM16_CH1, TIM1_CH2N, USART1_RTS_DE, COMP2_OUT, CAN_TX, TIM1_ETR, HRTIM1_FLT1, EVENTOUT	-

Table 13. STM32F334x4/6/8 pin definitions (continued)



Pi	n Numb	er				Pin	functions
LQFP 32	LQFP 48	LQFP 64	Pin name (function after reset)	Pin type	I/O structure	Alternate functions	Additional functions
28	41	57	PB5	I/O	FT	TIM16_BKIN, TIM3_CH2, I2C1_SMBA, SPI1_MOSI, USART2_CK, TIM17_CH1, HRTIM1_EEV6, EVENTOUT	-
29	42	58	PB6	I/O	FTf	TIM16_CH1N, TSC_G5_IO3, I2C1_SCL, USART1_TX, HRTIM1_SCIN, HRTIM1_EEV4, EVENTOUT	-
30	43	59	PB7	I/O	FTf	TIM17_CH1N, TSC_G5_IO4, I2C1_SDA, USART1_RX, TIM3_CH4, HRTIM1_EEV3, EVENTOUT	-
31	44	60	BOOT0	I	В	-	-
-	45	61	PB8	I/O	FTf	TIM16_CH1, TSC_SYNC,I2C1_SCL, USART3_RX,CAN_RX, TIM1_BKIN, HRTIM1_EEV8, EVENTOUT	-
-	46	62	PB9	I/O	FTf	TIM17_CH1, I2C1_SDA, IR_OUT, USART3_TX, COMP2_OUT, CAN_TX, HRTIM1_EEV5, EVENTOUT_	-
32	47	63	VSS	S	-	-	-
1	48	64	VDD	S	-	-	-

Table 13	STM32F334x4/6/8	nin definitions ((continued)
			continucu)

1.

PC13, PC14 and PC15 are supplied through the power switch. Since the switch sinks only a limited amount of current (3 mA), the use of GPIO PC13 to PC15 in output mode is limited: - The speed should not exceed 2 MHz with a maximum load of 30 pF - These GPIOs must not be used as current sources (e.g. to drive an LED). After the first backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the Backup registers which is not reset by the main reset. For details on how to manage these GPIOs, refer to the Battery backup domain and BKP register description sections in the reference manual.

2. Fast ADC channel.

3. These GPIOs offer a reduced touch sensing sensitivity. It is thus recommended to use them as sampling capacitor I/O.



6.1.7 Measurement of the current consumption



Figure 11. Scheme of the current-consumption measurement



6.3 Operating conditions

6.3.1 General operating conditions

Symbol	Parameter	Conditions	Min.	Max.	Unit			
f _{HCLK}	Internal AHB clock frequency	-	0	72				
f _{PCLK1}	Internal APB1 clock frequency	-	0	36	MHz			
f _{PCLK2}	Internal APB2 clock frequency	-	0	72				
V _{DD}	Standard operating voltage	-	2	3.6				
V _{DD18}	Core, SRAM and Flash memory power supply	-	1.65	1.95				
V	Analog operating voltage (OPAMP and DAC not used)	Must have a potential equal to	2	3.6	V			
V DDA	Analog operating voltage (OPAMP and DAC used)	or higher than V _{DD}	2.4	3.6				
V _{BAT}	Backup operating voltage	-	1.65	3.6	V			
		TC I/O	-0.3	V _{DD} +0.3				
		TT I/O	-0.3	3.6	V			
V _{IN}	I/O input voltage	TTa I/O	-0.3	V _{DDA} +0.3				
		FT and FTf I/O ⁽¹⁾	-0.3	5.5	V			
		BOOT0	0	5.5				
PD	Power dissipation at $T_A = 85$ °C for suffix 6 or $T_A = 105$ °C for suffix $7^{(2)}$	LQFP64	-	444	mW			
PD	Power dissipation at $T_A = 85$ °C for suffix 6 or $T_A = 105$ °C for suffix $7^{(2)}$	LQFP48	-	364	mW			
PD	Power dissipation at $T_A = 85$ °C for suffix 6 or $T_A = 105$ °C for suffix 7	LQFP32	-	333	mW			
	Ambient temperature for 6 suffix	Maximum power dissipation	-40	85	°C			
T۵	version	Low power dissipation ⁽³⁾	-40	105	C			
IA	Ambient temperature for 7 suffix	Maximum power dissipation	-40	105	ംറ			
	version	Low power dissipation ⁽³⁾	-40	125				
T.	lunction temperature range	6 suffix version	-40	105	°۲			
IJ		7 suffix version	uffix version -40 125					

Table 19. General operating conditions

1. To sustain a voltage higher than V_{DD} +0.3 V, the internal pull-up/pull-down resistors must be disabled.

If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see Section Table 78.: Package thermal characteristics).

 In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see Section 7.5: Thermal characteristics).



							-					
					V _{DDA}	= 2.4 V			V _{DDA}	_= 3.6 V		
Symbol	Parameter	arameter Conditions	f _{HCLK}	Max. @ T _A ⁽²⁾			(2)	Typ	М	Unit		
				iyp.	25 °C	85 °C	105 °C	тур.	25 °C	85 °C	105 °C	
			72 MHz	224	252 ⁽³⁾	265	269 ⁽³⁾	245	272 ⁽³⁾	288	295 ⁽³⁾	
			64 MHz	196	225	237	241	214	243	257	263	
			48 MHz	147	174	183	186	159	186	196	201	
	Supply	bly HSE bypass leep e, e	32 MHz	100	126	133	135	109	133	142	145	
	current in Run/Sleep		24 MHz	79	102	107	108	85	108	113	116	
	mode,		8 MHz	3	5	5	6	4	6	6	7	
'DDA	code		1 MHz	3	5	5	6	3	5	6	6	μΑ
	from Flash		64 MHz	259	288	304	309	285	315	332	338	
	or RAM		48 MHz	208	239	251	254	230	258	271	277	
		HSI clock	32 MHz	162	190	198	202	179	206	216	219	
			24 MHz	140	168	175	178	155	181	188	191	
			8 MHz	62	85	88	89	71	94	96	98	

Table 26. Typical and maximum current consumption from the V_{DDA} supply

1. Current consumption from the V_{DDA} supply is independent of whether the peripherals are on or off. Furthermore when the PLL is off, I_{DDA} is independent from the frequency.

2. Data based on characterization results, not tested in production.

3. Data based characterization results and tested in production with code executing from RAM.

				Тур. (@V _{DD}	(V _{DD} =\						
Symbol	Parameter	Conditions	2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T _A = 25 °C	T _A = 85 °C	T _A = 105 ° C	Unit
I _{DD}	Supply current in Stop mode	Regulator in run mode, all oscillators OFF	17.5 1	17.6 8	17.8 4	18.1 7	18.5 7	19.3 9	30.6	232.5	612.2	
		Regulator in low-power mode, all oscillators OFF	6.44	6.51	6.60	6.73	6.96	7.20	20.0	246.4	585.0	μA
	Supply current in Standby mode	LSI ON and IWDG ON	0.73	0.89	1.02	1.14	1.28	1.44	-	-	-	
		LSI OFF and IWDG OFF	0.55	0.66	0.75	0.85	0.93	1.01	4.9	7.0	7.9	

Table 27. Typical and maximum V_{DD} consumption in Stop and Standby modes

1. Data based on characterization results, not tested in production unless otherwise specified.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 33: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

 I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: C = C_{INT} + C_{EXT+CS}



On-chip peripheral current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input configuration
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption:
 - With all peripherals clocked off
 - With only one peripheral clocked on
- Ambient operating temperature at 25°C and $V_{DD} = V_{DDA} = 3.3 V$

Table 33. Peripheral current consumption

Devicehovel	Typical consumption ⁽¹⁾	11	
Peripheral	I _{DD}	Onit	
BusMatrix ⁽²⁾	11.1	µA/MHz	
DMA1	8.0	-	
CRC	2.1	-	
GPIOA	8.7	-	
GPIOB	8.4	-	
GPIOC	8.4	-	
GPIOD	2.6	-	
GPIOF	1.7	-	
TSC	4.7	-	
ADC1&2	17.4	-	
APB2-Bridge ⁽³⁾	3.3	-	
SYSCFG	4.2	-	
TIM1	32.3	-	
USART1	20.3	-	
TIM15	13.8	-	
TIM16	9.7	-	
TIM17	10.3	-	
HRTIM	324.2	-	
APB1-Bridge ⁽³⁾	5.3	-	
TIM2	43.4	-	
TIM3	34.0	-	
TIM6	9.7	-	
TIM7	10.3	-	
WWDG	6.9	-	
USART2	18.8	-	
USART3	19.1	-	



Porinhoral	Typical consumption ⁽¹⁾	Unit				
renpheral	I _{DD}	onit				
I2C1	13.3	-				
CAN	31.3	-				
PWR	4.7	-				
DAC	15.4	-				
DAC2	8.6	-				
SPI1	8.2	-				

Table 33. Peripheral current consumption (continued)

1. The power consumption of the analog part (I_{DDA}) of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.

2. BusMatrix is automatically active when at least one master is ON (CPU or DMA1).

3. The APBx bridge is automatically active when at least one peripheral is ON on the same bus.



Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
f _{HSE_ext}	User external clock source frequency ⁽¹⁾	1	8	32	MHz	
V _{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V _{DD}	V
V _{HSEL}	OSC_IN input pin low level voltage	-	V _{SS}	-	$0.3V_{DD}$	v
t _{w(HSEH)} t _{w(HSEL)}	OSC_IN high or low time ⁽¹⁾		15	-	-	ne
t _{r(HSE)} t _{f(HSE)}	OSC_IN rise or fall time ⁽¹⁾		-	-	20	115

Fable 36. High-speed	l external user	clock characteristics
----------------------	-----------------	-----------------------

1. Guaranteed by design, not tested in production.





Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 14*

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
f _{LSE_ext}	User External clock source frequency ⁽¹⁾	er External clock source quency ⁽¹⁾			1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage	C32_IN input pin high level			V _{DD}	V
V _{LSEL}	OSC32_IN input pin low level voltage	2_IN input pin low level			0.3V _{DD}	v
t _{w(LSEH)} t _{w(LSEL)}	OSC32_IN high or low time ⁽¹⁾	32_IN high or low time ⁽¹⁾		-	-	ne
t _{r(LSE)} t _{f(LSE)}	SC32_IN rise or fall time ⁽¹⁾		-	-	50	115

Table 37. Low-speed external user clock characteristics

1. Guaranteed by design, not tested in production.





Figure 14. Low-speed external clock source AC timing diagram

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 38*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽¹⁾	Min. ⁽²⁾	Тур.	Max. ⁽²⁾	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
		During startup ⁽³⁾	-	-	8.5	
	I _{DD} HSE current consumption	V _{DD} = 3.3 V, Rm= 30Ω CL=10 pF@8 MHz	-	0.4	-	
		V _{DD} = 3.3 V, Rm= 45Ω CL=10 pF@8 MHz	-	0.5	-	
I _{DD}		V _{DD} = 3.3 V, Rm= 30Ω, CL=5 pF@32 MHz	-	0.8	-	mA
		V _{DD} = 3.3 V, Rm= 30Ω CL=10 pF@32 MHz	-	1	-	
		V _{DD} = 3.3 V, Rm= 30Ω CL=20 pF@32 MHz	-	1.5	-	
9 _m	Oscillator transconductance	Startup	10	-	-	mA/V
t _{SU(HSE)} ⁽⁴⁾	Startup time	V _{DD} is stabilized	-	2	-	ms

Table 38. HSE oscillator characteristics

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

2. Guaranteed by design, not tested in production.

- 3. This consumption level occurs during the first 2/3 of the $t_{SU(\text{HSE})}$ startup time.
- t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.





Figure 31. Maximum V_{REFINT} scaler startup time from power-down

6.3.22 Operational amplifier characteristics

Symbol	Parameter		Condition	Min.	Тур.	Max.	Unit
V _{DDA}	Analog supply voltage		-	2.4	-	3.6	V
CMIR	Common mode inpu	t range	-	0	-	V _{DDA}	V
	Maximum		25°C, No Load on output.	-	-	4	
M		calibration range	All voltage/Temp.	-	-	6	m)/
VIOFFSET	VI _{OFFSET} Input offset voltage	After offset	25°C, No Load on output.	-	-	1.6	mv
		calibration	All voltage/Temp.	-	-	3	
ΔVI_{OFFSET}	Input offset voltage drift		-	-	5	-	µV/°C
I _{LOAD}	Drive current		-	-	-	500	μA
IDDOPAMP	Consumption		No load, quiescent mode	-	690	1450	μA
CMRR	Common mode rejection ratio		-	-	90	-	dB
PSRR	Power supply rejection ratio		DC	73	117	-	dB
GBW	Bandwidth		-	-	8.2	-	MHz
SR	Slew rate		-	-	4.7	-	V/µs
R _{LOAD}	Resistive load		-	4	-	-	kΩ
C _{LOAD}	Capacitive load		-	-	-	50	pF

Table 71	. Operational	amplifier	characteristics ⁽¹)
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Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit	
VOH	High acturation voltage ⁽²⁾	R _{load} = min, Input at V _{DDA} .	V _{DDA} -100	-			
VONSAT	nigh saturation voltage	R _{load} = 20K, Input at V _{DDA} .	V _{DDA} -20	-			
VO		R _{load} = min, input at 0 V	-	-	100	mV	
VOLSAT	VOL _{SAT} Low saturation voltage		-	-	20		
φm	Phase margin	-	-	62	-	0	
tofftrim	Offset trim time: during calibration, minimum time needed between two steps to have 1 mV accuracy	-	-	-	2	ms	
twakeup	Wake up time from OFF state.	$\begin{array}{l} C_{LOAD} \leq \!\! 50 \text{ pf}, \\ R_{LOAD} \geq 4 k\Omega \\ \text{Follower} \\ \text{configuration} \end{array}$	-	2.8	5	μs	
ts_opam_vout	ADC sampling time when reading the OPAMP output		400	-	-	ns	
	Non inverting gain value		-	2	-	-	
		-	-	4	-	-	
r GA yan			-	8	-	-	
			-	16	-	-	
		Gain=2	-	5.4/5.4	-	kΩ	
Б	R2/R1 internal resistance values in PGA mode $^{(3)}$	Gain=4	-	16.2/5.4	-		
Rnetwork		Gain=8	-	37.8/5.4	-		
		Gain=16	-	40.5/2.7	-		
PGA gain error	PGA gain error	-	-1%	-	1%	-	
I _{bias}	OPAMP input bias current	-	-	-	±0.2 ⁽⁴⁾	μA	
PGA BW		PGA Gain = 2, C _{load} = 50pF, R _{load} = 4 K Ω	-	4	-		
	PGA bandwidth for different non inverting gain	PGA Gain = 4, C_{load} = 50pF, R_{load} = 4 K Ω	-	2	-	MHz	
		PGA Gain = 8, C_{load} = 50pF, R_{load} = 4 K Ω	-	1	-		
		PGA Gain = 16, C_{load} = 50pF, R_{load} = 4 K Ω	-	0.5	-		

Table 71. Operational am	plifier characteristics ⁽¹⁾ ((continued)
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7.3 LQFP48 package information

LQFP48 is a 48-pin, 7 x 7mm low-profile quad flat package.



Figure 36. LQFP48 package outline

1. Drawing is not to scale.

Table 76. LQFP48 package mechanical data

Symbol		millimeters			inches ⁽¹⁾		
Symbol	Min	Тур	Мах	Min	Тур	Мах	
А	-	-	1.600	-	-	0.0630	
A1	0.050	-	0.150	0.0020	-	0.0059	
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571	
b	0.170	0.220	0.270	0.0067	0.0087	0.0106	
с	0.090	-	0.200	0.0035	-	0.0079	
D	8.800	9.000	9.200	0.3465	0.3543	0.3622	
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835	
D3	-	5.500	-	-	0.2165	-	



9 Revision history

Date	Revision	Changes
19-Jun-2014	1	Initial release.
09-Dec-2014	2	Updated: Table 54: TIMx characteristics Table 14: STM32F303x6/8 pin definitions Table 59: ADC characteristics Table 34: Peripheral current consumption Table 40: HSI oscillator characteristics Table 17: HSI oscillator accuracy characterization results for soldered parts Table 2: STM32F334x4/6/8 family device features and peripheral counts
2-Feb-2015	3	Updated: Figure 1: STM32F334x4/6/8 block diagram Table 38: HSE oscillator characteristics Table 43: Flash memory characteristics Added Figure 13: High-speed external clock source AC timing diagram
09-Jun-2015	4	Udpated : Title Section 3.14.1: 217 ps high-resolution timer (HRTIM1) Section 6.1.6: Power-supply scheme Table 19: General operating conditions
27-Sep-2016	5	Updated: Section Table 69.: DAC characteristics, Section Table 64.: ADC characteristics, Table 53: NRST pin characteristics, Figure 2: Clock tree, Table 13: STM32F334x4/6/8 pin definitions, Table 71: Operational amplifier characteristics, Figure 20: Five volt tolerant (FT and FTf) I/O input characteristics - CMOS port, Table 23: Embedded internal reference voltage, Table 39: LSE oscillator characteristics (fLSE = 32.768 kHz) Added: Table 35: Wakeup time using USART

Table 80. Document revision history

